



General Description:

- (1) Chip Dimension
 Chip Size= 13.3 mil x 15.8 mil (340um x 400um)
 Chip Thickness = 90±10µm
 P/N Bonding Pad = 85±5µm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics(Ta=RT)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V _F	2.8	-	3.5	V	I _F =20mA
Dominant Wavelength	λ _D	450	460	470	nm	I _F =20mA
Reverse Current	I _R	0	-	1	µA	V _R =-5V

Luminous Intensity(I _v) mcd at I _F =20mA	Dominant Wavelength(nm)												
	Range	445~447.5	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465	465~467.5	467.5~470	470~472.5	472.5~475
80-90													
90-100			*	*									
100-120			*	*	*								
120-140				*	*	*	*	*					
140-160				*	*	*	*	*					
160-180					*	*	*	*	*				
180-200						*	*	*	*				
200-240								*	*	*	*		

Features:

- 1. High Luminous Intensity
- 2. Long Operation Life
- 3. High Current; Pulse Operation
- 4. Indoor/Outdoor Applications

Notes:

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error of ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD